

Silicon NPN Power Transistors

2SC2688

DESCRIPTION

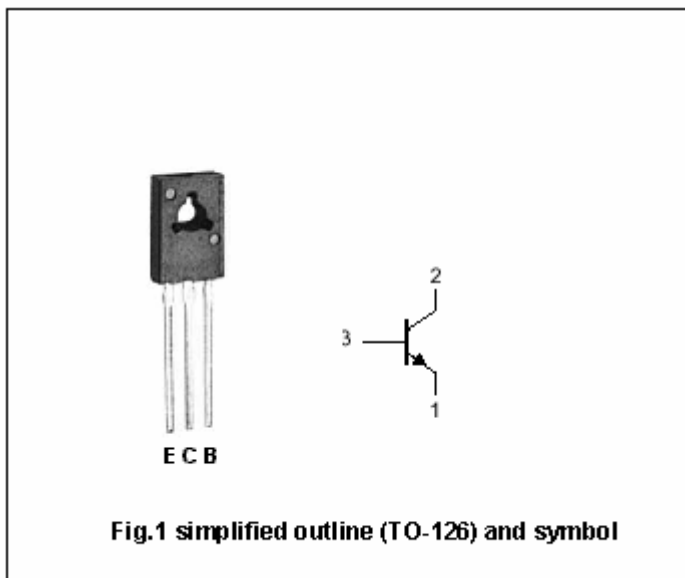
- With TO-126 package
- High breakdown voltage
- High transition frequency

APPLICATIONS

- Designed for use in Color TV chroma output circuits.

PINNING

| PIN | DESCRIPTION |
|-----|--------------------------------------|
| 1 | Emitter |
| 2 | Collector;connected to mounting base |
| 3 | Base |



Absolute maximum ratings(Ta=25°C)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|------------------|-----------------------------|----------------------|---------|------|
| V _{CBO} | Collector-base voltage | Open emitter | 300 | V |
| V _{CEO} | Collector-emitter voltage | Open base | 300 | V |
| V _{EBO} | Emitter-base voltage | Open collector | 5 | V |
| I _C | Collector current | | 0.2 | A |
| P _C | Collector power dissipation | T _a =25°C | 1.25 | W |
| | | T _C =25°C | 10 | |
| T _j | Junction temperature | | 150 | °C |
| T _{stg} | Storage temperature | | -55~150 | °C |

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|---|-----|------|-----|------|
| V _{CEsat} | Collector-emitter saturation voltage | I _C =50mA; I _B =5mA | | | 1.5 | V |
| V _{(BR)CEO} | Collector-emitter breakdown voltage | I _C =1mA; I _B =0 | 300 | | | V |
| I _{CBO} | Collector cut-off current | V _{CB} =200V; I _E =0 | | | 0.1 | μA |
| I _{EBO} | Emitter cut-off current | V _{EB} =5V; I _C =0 | | | 0.1 | μA |
| h _{FE} | DC current gain | I _C =10mA; V _{CE} =10V | 40 | | 250 | |
| f _T | Transition frequency | I _C =10mA; V _{CE} =30V | 40 | | | MHz |
| C _{re} | Feedback capacitance | I _E =0; V _{CB} =10V; f=1MHz | | | 3.0 | pF |

◆ h_{FE} Classifications

| N | M | L | K |
|-------|--------|---------|---------|
| 40-80 | 60-120 | 100-200 | 160-250 |

